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1 Ω Typical On Resistance, ±5 V, +12 V, +5 V, and +3.3 V Dual SPDT Switches

Data Sheet

FEATURES

1 Ω typical on resistance
0.2 Ω on resistance flatness
±3.3 V to ±8 V dual supply operation
3.3 V to 16 V single supply operation
No V_L supply required
3 V logic-compatible inputs
Rail-to-rail operation
Continuous current per channel
LFCSP: 385 mA
TSSOP: 238 mA
16-lead TSSOP and 16-lead, 4 mm × 4 mm LFCSP

APPLICATIONS

Communication systems Medical systems Audio signal routing Video signal routing Automatic test equipment Data acquisition systems Battery-powered systems Sample-and-hold systems Relay replacements

ADG1636

FUNCTIONAL BLOCK DIAGRAMS

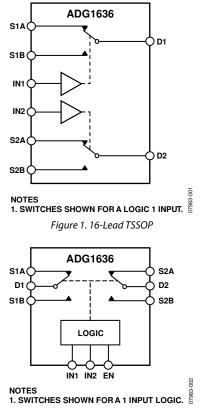


Figure 2. 16-Lead LFCSP

GENERAL DESCRIPTION

The ADG1636 is a monolithic CMOS device containing two independently selectable single-pole/double-throw (SPDT) switches. An EN input is used to enable or disable the device. When disabled, all channels are switched off. Each switch conducts equally well in both directions when on and has an input signal range that extends to the supplies. In the off condition, signal levels up to the supplies are blocked. Both switches exhibit break-before-make switching action for use in multiplexer applications.

The ultralow on resistance of these switches make them ideal solutions for data acquisition and gain switching applications where low on resistance and distortion is critical. The on resistance profile is very flat over the full analog input range, ensuring excellent linearity and low distortion when switching audio signals.

The CMOS construction ensures ultralow power dissipation, making the devices ideally suited for portable and batterypowered instruments.

PRODUCT HIGHLIGHTS

- 1. 1.6 Ω maximum on resistance over temperature.
- 2. Minimum distortion: THD + N = 0.007%.
- 3. 3 V logic-compatible digital inputs: $V_{INH} = 2.0$ V, $V_{INL} = 0.8$ V.
- 4. No V_L logic power supply required.
- 5. Ultralow power dissipation: <16 nW.
- 6. 16-lead TSSOP and 16-lead 4 mm \times 4 mm LFCSP.

Rev. B

Document Feedback

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ADG1636* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

COMPARABLE PARTS

View a parametric search of comparable parts.

EVALUATION KITS

 Evaluation Board for 16 lead TSSOP Devices in the Switch/ Mux Portfolio

DOCUMENTATION

Data Sheet

- ADG1636: 1 Ω Typical On Resistance, ±5 V, +12 V, +5 V, and +3.3 V Dual SPDT Switches Data Sheet

User Guides

• UG-945: Evaluation Board for 16-Lead TSSOP Devices in the Switches and Multiplexers Portfolio

REFERENCE DESIGNS

• CN0125

REFERENCE MATERIALS

Informational

• iCMOS Technology Enabling the +/-10V World

Product Selection Guide

• Switches and Multiplexers Product Selection Guide

DESIGN RESOURCES

- ADG1636 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

DISCUSSIONS

View all ADG1636 EngineerZone Discussions.

SAMPLE AND BUY

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REVISION HISTORY

3/16—Rev. A to Rev. B

Changed CP-16-13 to CP-16-26	Throughout
Changes to Figure 3, Figure 4, and Table 7	
Updated Outline Dimensions	
Changes to Ordering Guide	
9/09—Rev. 0 to Rev. A	

(Change	es to	Table	4	5

1/09—Revision 0: Initial Version

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SPECIFICATIONS

±5 V DUAL SUPPLY

 V_{DD} = +5 V \pm 10%, V_{SS} = -5 V \pm 10%, GND = 0 V, unless otherwise noted.

Table 1.

Parameter	25°C	–40°C to +85°C	–40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V_{DD} to V_{SS}	V	
On Resistance (R _{ON})	1			Ωtyp	$V_{s} = \pm 4.5 V$, $I_{s} = -10 mA$; see Figure 23
	1.2	1.4	1.6	Ωmax	$V_{DD} = \pm 4.5 \text{ V}, V_{SS} = \pm 4.5 \text{ V}$
On Resistance Match Between Channels (ΔR_{ON})	0.04			Ωtyp	$V_{s} = \pm 4.5 V$, $I_{s} = -10 mA$
	0.08	0.09	0.1	Ωmax	
On Resistance Flatness (R _{FLAT(ON)})	0.2			Ωtyp	$V_{s} = \pm 4.5 V$, $I_{s} = -10 mA$
	0.25	0.29	0.34	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = +5.5 V, V_{SS} = -5.5 V$
Source Off Leakage, Is (Off)	±0.1			nA typ	$V_{s} = \pm 4.5 V, V_{D} = \mp 4.5 V$; see Figure 24
-	±0.25	±1	±4	nA max	
Drain Off Leakage, I _D (Off)	±0.1			nA typ	$V_{s} = \pm 4.5V, V_{D} = \mp 4.5V;$ see Figure 24
	±0.25	±2	±10	nA max	
Channel On Leakage, I _D , Is (On)	±0.3			nA typ	$V_s = V_D = \pm 4.5 V$; see Figure 25
· · · · · · · · · · · · · · · · · · ·	±0.6	±2	±12	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, I _{INL} or I _{INH}	0.005			μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
			±0.1	µA max	
Digital Input Capacitance, C _{IN}	5			pF typ	
DYNAMIC CHARACTERISTICS ¹				. ,	
Transition Time, transition	130			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	209	245	273	ns max	$V_s = 2.5 V$; see Figure 30
t _{on} (EN)	119			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	148	166	176	ns max	$V_s = 2.5 V$; see Figure 30
t _{off} (EN)	182			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	228	259	281	ns max	$V_s = 2.5 V$; see Figure 30
Break-Before-Make Time Delay, t _D	30			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
			17	ns min	$V_{s1} = V_{s2} = 2.5 V$; see Figure 31
Charge Injection	130			pC typ	$V_s = 0 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 32
Off Isolation	70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 26
Channel-to-Channel Crosstalk	90			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 28
Total Harmonic Distortion + Noise (THD + N)	0.007			% typ	$R_L = 110 \Omega$, 5 V p-p, f = 20 Hz to 20 kHz; see Figure 29
–3 dB Bandwidth	25			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 27
Cs (Off)	68			pF typ	$V_{s} = 0 V, f = 1 MHz$
C_{D} (Off)	127			pF typ	$V_{s} = 0 V, f = 1 MHz$
C _D , C _s (On)	220			pF typ	$V_{s} = 0 V, f = 1 MHz$
POWER REQUIREMENTS	1				$V_{DD} = +5.5 V, V_{SS} = -5.5 V$
I _{DD}	0.001			μA typ	Digital inputs = $0 \text{ V or } V_{DD}$
			1.0	µA max	
V _{DD} /V _{SS}			±3.3/±8	V min/max	

12 V SINGLE SUPPLY

 V_{DD} = 12 V \pm 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 2.

		–40°C to	–40°C to		
Parameter	25°C	+85°C	+125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V _{DD}	V	
On Resistance (R _{ON})	0.95			Ωtyp	$V_s = 0 V$ to $10 V$, $I_s = -10 mA$; see Figure 23
	1.1	1.25	1.45	Ωmax	$V_{DD} = 10.8 V, V_{SS} = 0 V$
On Resistance Match Between Channels (ΔR_{ON})	0.03			Ωtyp	$V_s = 10 V$, $I_s = -10 mA$
	0.06	0.07	0.08	Ωmax	
On Resistance Flatness (R _{FLAT(ON)})	0.2			Ωtyp	$V_s = 0 V$ to 10 V, $I_s = -10 mA$
	0.23	0.27	0.32	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = 13.2 \text{ V}, V_{SS} = 0 \text{ V}$
Source Off Leakage, Is (Off)	±0.1			nA typ	$V_{s} = 1 \text{ V}/10 \text{ V}, V_{s} = 10 \text{ V}/1 \text{ V}; \text{ see Figure 24}$
	±0.25	±1	±4	nA max	
Drain Off Leakage, I _D (Off)	±0.1			nA typ	$V_s = 1 V/10 V$, $V_s = 10 V/1 V$; see Figure 24
	±0.25	±2	±10	nA max	
Channel On Leakage, I _D , I _S (On)	±0.3			nA typ	$V_s = V_D = 1 V$ or 10 V; see Figure 25
	±0.6	±2	±12	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, line or linh	0.001			µA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
			±0.1	µA max	
Digital Input Capacitance, C _{IN}	5		_0.1	pF typ	
DYNAMIC CHARACTERISTICS ¹	5			p. 9p	
Transition Time, transition	100			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	153	183	206	ns max	$V_s = 8 V$; see Figure 30
ton (EN)	80	105	200	ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	95	103	110	ns max	$V_s = 8 V$; see Figure 30
toff (EN)	133	105	110	ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	161	187	210	ns max	$V_s = 8 V$; see Figure 30
Break-Before-Make Time Delay, t₀	25	107	210		$R_L = 300 \Omega$, $C_L = 35 pF$
break-belore-make time Delay, to	25		17	ns typ	$V_{s1} = V_{s2} = 8 V$; see Figure 31
Channes Inite stiller	150		17	ns min	_
Charge Injection	150			pC typ	$V_s = 6 V, R_s = 0 \Omega, C_L = 1 nF$; see Figure 32
Off Isolation	70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 26
Channel-to-Channel Crosstalk	90			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 28
Total Harmonic Distortion + Noise (THD + N)	0.013			% typ	R_L = 110 $\Omega,$ 5 V p-p, f = 20 Hz to 20 kHz; see Figure 29
–3 dB Bandwidth	27			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 27
C _s (Off)	65			pF typ	$V_{s} = 6 V, f = 1 MHz$
C _D (Off)	120			pF typ	$V_{s} = 6 V, f = 1 MHz$
C _D , C _s (On)	216			pF typ	$V_{s} = 6 V, f = 1 MHz$
POWER REQUIREMENTS					$V_{DD} = 12 V$
IDD	0.001			μA typ	Digital inputs = $0 V$ or V_{DD}
			1	µA max	
ldd	230		-	μA typ	Digital inputs = 5 V
	200		360	μA max	
V _{DD}			3.3/16	V min/max	
V DD			5.5/10	v min/max	

5 V SINGLE SUPPLY

 V_{DD} = 5 V \pm 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 3.

Parameter	25°C	–40°C to +85°C	–40°C to 125°C	Unit	Test Conditions/Comments
ANALOG SWITCH	25 C	το ς τ	125 C	Unit	
Analog Signal Range			0 V to V _{DD}	v	
On Resistance (R _{on})	1.7		0 1 10 100	Ω typ	$V_s = 0 V$ to 4.5 V, $I_s = -10 mA$; see Figure 23
	2.15	2.4	2.7	Ωmax	$V_{DD} = 4.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V}$
On Resistance Match Between Channels (ΔR_{ON})	0.05		2.7	Ωtyp	$V_s = 0 V \text{ to } 4.5 V, I_s = -10 \text{ mA}$
	0.09	0.12	0.15	Ωmax	
On Resistance Flatness (R _{FLAT(ON)})	0.4	0112	0110	Ωtyp	$V_s = 0 V$ to 4.5 V, $I_s = -10 mA$
	0.53	0.55	0.6	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = 5.5 V, V_{SS} = 0 V$
Source Off Leakage, Is (Off)	±0.05			nA typ	$V_s = 1 V/4.5 V$, $V_D = 4.5 V/1 V$; see Figure 24
	±0.25	±1	±4	nA max	
Drain Off Leakage, I _D (Off)	±0.05			nA typ	$V_s = 1 V/4.5 V$, $V_D = 4.5 V/1 V$; see Figure 24
	±0.25	±2	±10	nA max	
Channel On Leakage, I _D , I _S (On)	±0.1			nA typ	$V_s = V_D = 1 V \text{ or } 4.5 V$; see Figure 25
	±0.6	±2	±12	nA max	······································
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, Inc or Inh	0.001			μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
			±0.1	µA max	
Digital Input Capacitance, C _{IN}	5			pF typ	
DYNAMIC CHARACTERISTICS ¹					
Transition Time, transition	160			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	271	319	355	ns max	$V_s = 2.5 V$; see Figure 30
t _{on} (EN)	132			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	172	185	201	ns max	V _s = 2.5 V; see Figure 30
t _{off} (EN)	210			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	268	313	345	ns max	$V_s = 2.5 V$; see Figure 30
Break-Before-Make Time Delay, t₀	30			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
			17	ns min	$V_{s1} = V_{s2} = 2.5 V$; see Figure 31
Charge Injection	70			pC typ	$V_s = 2.5 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 32
Off Isolation	70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 26
Channel-to-Channel Crosstalk	90			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 28
Total Harmonic Distortion + Noise (THD + N)	0.09			% typ	R_L = 110 $\Omega,$ f = 20 Hz to 20 kHz, Vs = 3.5 V p-p; see Figure 29
–3 dB Bandwidth	26			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 27
C _s (Off)	76			pF typ	$V_s = 2.5 V, f = 1 MHz$
C_{D} (Off)	145			pF typ	$V_s = 2.5 V, f = 1 MHz$
C _D , C _s (On)	237			pF typ	$V_s = 2.5 V, f = 1 MHz$
POWER REQUIREMENTS					$V_{DD} = 5.5 V$
ldd	0.001			µA typ	Digital inputs = $0 V \text{ or } V_{DD}$
		1.0	1.0	µA max	
V _{DD}			3.3/16	V min/max	

3.3 V SINGLE SUPPLY

 V_{DD} = 3.3 V, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 4.

Parameter	25°C	–40°C to +85°C	–40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V _{DD}	v	
On Resistance (R _{ON})	3.2	3.4	3.6	Ω typ	$V_s = 0 V$ to V_{DD} , $I_s = -10 mA$; see Figure 23
					$V_{DD} = 3.3 V, V_{SS} = 0 V$
On Resistance Match Between Channels (ΔR_{ON})	0.06	0.07	0.08	Ωtyp	$V_{s} = 0 V \text{ to } V_{DD}, I_{s} = -10 \text{ mA}$
On Resistance Flatness (R _{FLAT(ON)})	1.2	1.3	1.4	Ωtyp	$V_{s} = 0 V \text{ to } V_{DD}$, $I_{s} = -10 \text{ mA}$
LEAKAGE CURRENTS					$V_{DD} = 3.6 V, V_{SS} = 0 V$
Source Off Leakage, Is (Off)	±0.02			nA typ	$V_s = 0.6 V/3 V, V_D = 3 V/0.6 V$; see Figure 24
-	±0.25	±1	±4	nA max	
Drain Off Leakage, I _D (Off)	±0.02			nA typ	$V_s = 0.6 V/3 V, V_D = 3 V/0.6 V$; see Figure 24
	±0.25	±2	±10	nA max	
Channel On Leakage, I _D , I _s (On)	±0.05			nA typ	$V_{s} = V_{D} = 0.6 V$ or 3 V; see Figure 25
	±0.6	±2	±12	nA max	_
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
	0.001			μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
			±0.1	µA max	
Digital Input Capacitance, C _{IN}	5			pF typ	
DYNAMIC CHARACTERISTICS ¹					
Transition Time, transition	275			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	449	506	550	ns max	V _s = 1.5 V; see Figure 30
ton (EN)	225			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	306	327	338	ns max	V _s = 1.5 V; see Figure 30
t _{off} (EN)	340			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	454	512	553	ns max	V _s = 1.5 V; see Figure 30
Break-Before-Make Time Delay, t _D	50			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
			28	ns min	$V_{S1} = V_{S2} = 1.5 V$; see Figure 31
Charge Injection	50			pC typ	$V_s = 1.5 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 32
Off Isolation	70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 26
Channel-to-Channel Crosstalk	90			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 28
Total Harmonic Distortion + Noise (THD + N)	0.19			% typ	$R_L = 33 \Omega$, f = 20 Hz to 20 kHz, Vs = 2 V p-p; see Figure 29
–3 dB Bandwidth	26			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 27
C _s (Off)	80			pF typ	$V_s = 1.5 V, f = 1 MHz$
C _D (Off)	153			pF typ	$V_{s} = 1.5 V, f = 1 MHz$
C _D , C _S (On)	243			pF typ	$V_s = 1.5 V_r f = 1 MHz$
POWER REQUIREMENTS					V _{DD} = 3.6 V
lod	0.001			µA typ	Digital inputs = $0 V$ or V_{DD}
		1.0	1.0	µA max	
V _{DD}			3.3/16	V min/max	

CONTINUOUS CURRENT PER CHANNEL, S OR D

Table 5.

Parameter	25°C	85°C	125°C	Unit
CONTINUOUS CURRENT, S OR D				
$V_{DD} = +5 V, V_{SS} = -5 V$				
TSSOP ($\theta_{JA} = 150.4^{\circ}C/W$)	238	151	88	mA maximum
LFCSP ($\theta_{JA} = 48.7^{\circ}C/W$)	385	220	105	mA maximum
$V_{DD} = 12 V, V_{SS} = 0 V$				
TSSOP ($\theta_{JA} = 150.4^{\circ}C/W$)	280	175	98	mA maximum
LFCSP ($\theta_{JA} = 48.7^{\circ}C/W$)	469	259	119	mA maximum
$V_{DD} = 5 V, V_{SS} = 0 V$				
TSSOP ($\theta_{JA} = 150.4^{\circ}C/W$)	189	126	77	mA maximum
LFCSP ($\theta_{JA} = 48.7^{\circ}C/W$)	301	182	98	mA maximum
$V_{DD} = 3.3 V, V_{SS} = 0 V$				
TSSOP ($\theta_{JA} = 150.4^{\circ}C/W$)	189	130	84	mA maximum
LFCSP ($\theta_{JA} = 48.7^{\circ}C/W$)	305	189	105	mA maximum

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}C$, unless otherwise noted.

Table 6.

Table 0.							
Parameter	Rating						
V _{DD} to V _{SS}	18 V						
V _{DD} to GND	–0.3 V to +18 V						
Vss to GND	+0.3 V to -18 V						
Analog Inputs ¹	V _{ss} – 0.3 V to V _{DD} + 0.3 V or 30 mA, whichever occurs first						
Digital Inputs ¹	GND – 0.3 V to V _{DD} + 0.3 V or 30 mA, whichever occurs first						
Peak Current, S or D	850 mA (pulsed at 1 ms, 10% duty cycle maximum)						
Continuous Current, S or D ²	Data + 15%						
Operating Temperature Range							
Industrial (Y Version)	–40°C to +125°C						
Storage Temperature Range	–65°C to +150°C						
Junction Temperature	150°C						
θ _{JA} Thermal Impedance							
16-Lead TSSOP (2-Layer Board)	150.4°C/W						
16-Lead LFCSP (4-Layer Board)	48.7°C/W						
Reflow Soldering Peak Temperature, Pb free	260°C						

¹ Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

² See Table 5.

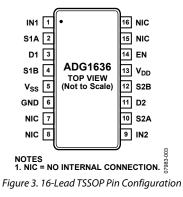
Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

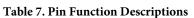
ESD CAUTION

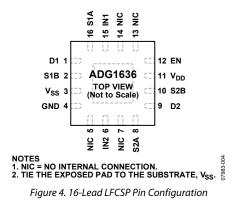


ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS







Pin No.		Pin No.			
TSSOP LFCSP		Mnemonic	Description		
1	15	IN1	Logic Control Input.		
2	16	S1A	Source Terminal. This pin can be an input or output.		
3	1	D1	Drain Terminal. This pin can be an input or output.		
4	2	S1B	Source Terminal. This pin can be an input or output.		
5	3	Vss	Most Negative Power Supply Potential.		
6	4	GND	Ground (0 V) Reference.		
7, 8, 15, 16	5, 7, 13, 14	NIC	No Internal Connection.		
9	6	IN2	Logic Control Input.		
10	8	S2A	Source Terminal. This pin can be an input or output.		
11	9	D2	Drain Terminal. This pin can be an input or output.		
12	10	S2B	Source Terminal. This pin can be an input or output.		
13	11	V _{DD}	Most Positive Power Supply Potential.		
14	12	EN	Active High Digital Input. When this pin is low, the device is disabled and all switches are off. When this pin is high, the Ax logic inputs determine the on switches.		
N/A ¹	0	EPAD	Exposed Pad. Tie the exposed pad to the substrate, Vss.		

¹ N/A means not applicable.

Table 8. ADG1636 TSSOP Truth Table

EN	INx	SxA	SxB
0	х	Off	Off
1	0	Off	On
1	1	On	Off

Table 9. ADG1636 LFCSP Truth Table

EN	INx	SxA	SxB
0	Х	Off	Off
1	0	Off	On
1	1	On	Off

TYPICAL PERFORMANCE CHARACTERISTICS

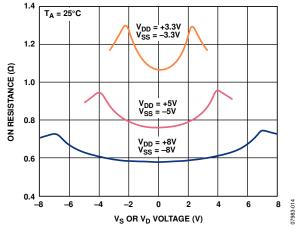


Figure 5. On Resistance as a Function of V_D (V_S) for Dual Supply

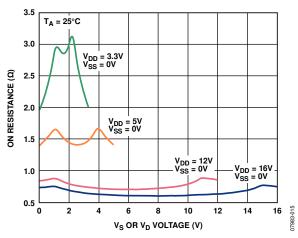


Figure 6. On Resistance as a Function of V_D (V_S) for Single Supply

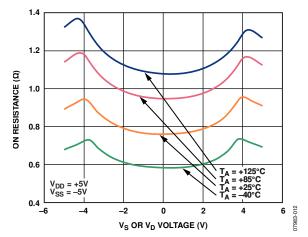


Figure 7. On Resistance as a Function of V_D (V₃) for Different Temperatures, ± 5 V Dual Supply

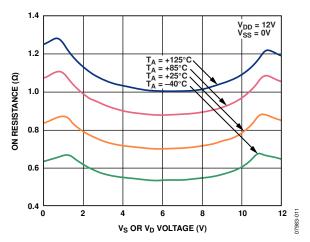


Figure 8. On Resistance as a Function of V_D (V_s) for Different Temperatures, 12 V Single Supply

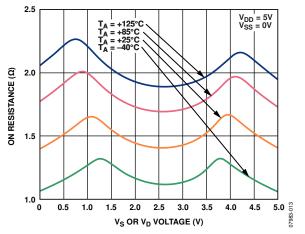


Figure 9. On Resistance as a Function of V_D (V_s) for Different Temperatures, 5 V Single Supply

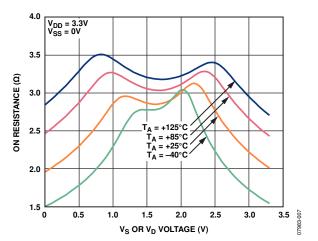


Figure 10. On Resistance as a Function of V_D (V_S) for Different Temperatures, 3.3 V Single Supply

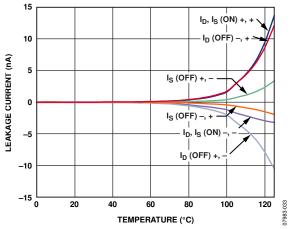


Figure 11. Leakage Currents as a Function of Temperature, ± 5 V Dual Supply

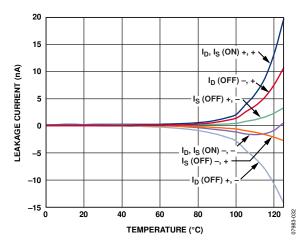


Figure 12. Leakage Currents as a Function of Temperature, 12 V Single Supply

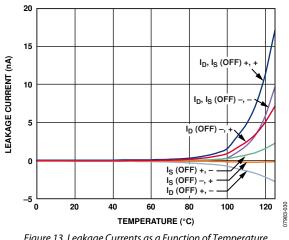


Figure 13. Leakage Currents as a Function of Temperature, 5 V Single Supply

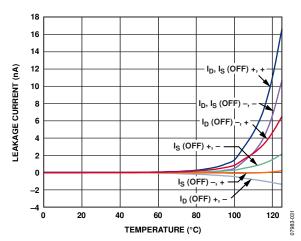
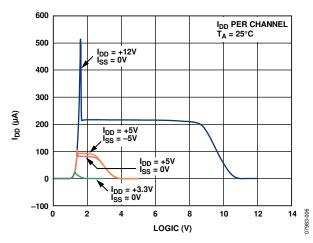
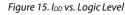


Figure 14. Leakage Currents as a Function of Temperature, 3.3 V Single Supply





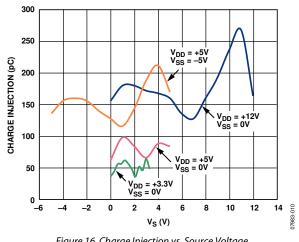
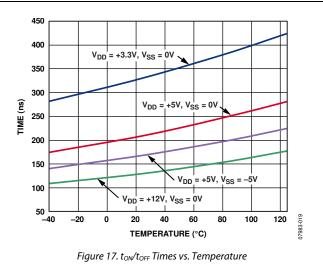


Figure 16. Charge Injection vs. Source Voltage



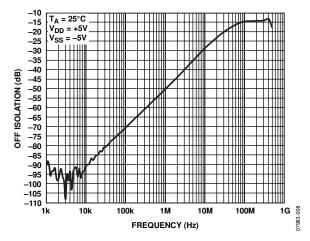


Figure 18. Off Isolation vs. Frequency

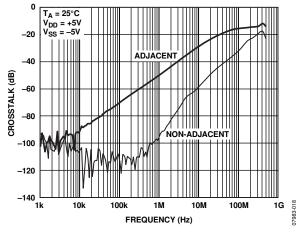
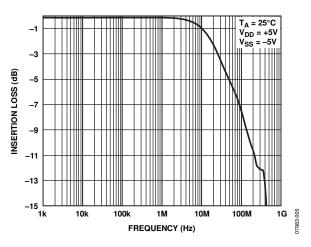
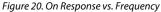
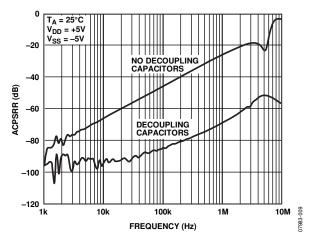


Figure 19. Crosstalk vs. Frequency









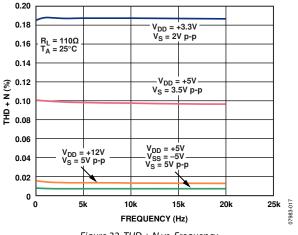
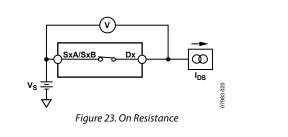
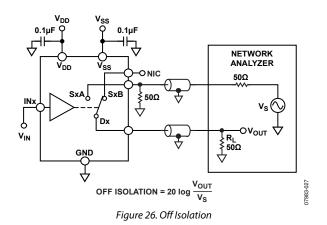


Figure 22. THD + N vs. Frequency

TEST CIRCUITS





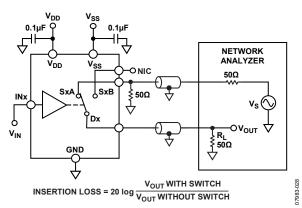
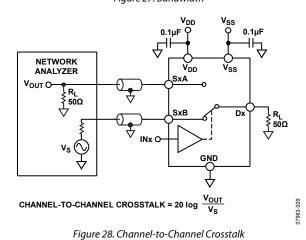
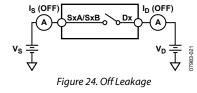
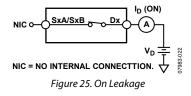
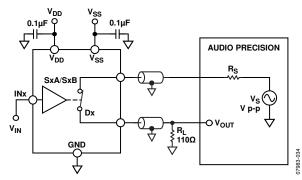


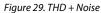
Figure 27. Bandwidth

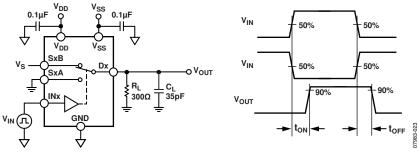




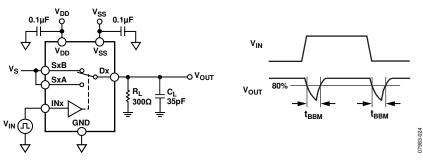


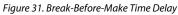












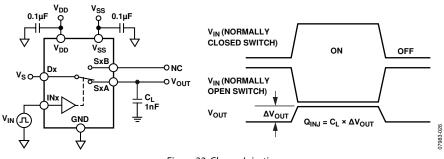


Figure 32. Charge Injection

TERMINOLOGY

Idd

The positive supply current.

Iss

The negative supply current.

 V_D (Vs) The analog voltage on Terminal D and Terminal S.

R_{ON} The ohmic resistance between Terminal D and Terminal S.

R_{FLAT(ON)} Flatness that is defined as the difference between the maximum and minimum value of on resistance measured over the specified analog signal range.

Is (Off) The source leakage current with the switch off.

 \mathbf{I}_{D} (Off) The drain leakage current with the switch off.

 $I_{\text{D}}, I_{\text{S}}\left(\text{On}\right)$ The channel leakage current with the switch on.

 \mathbf{V}_{INL} The maximum input voltage for Logic 0.

 \mathbf{V}_{INH} The minimum input voltage for Logic 1.

I_{INL} (I_{INH}) The input current of the digital input.

Cs (Off) The off switch source capacitance, which is measured with reference to ground.

 C_D (Off) The off switch drain capacitance, which is measured with reference to ground.

 C_D , C_S (On) The on switch capacitance, which is measured with reference to ground.

Cin

The digital input capacitance.

tTRANSITION

The delay time between the 50% and 90% points of the digital input and switch on condition when switching from one address state to another.

ton (EN)

The delay between applying the digital control input and the output switching on. See Figure 30.

toff (EN)

The delay between applying the digital control input and the output switching off. See Figure 30.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching.

Off Isolation A measure of unwanted signal coupling through an off switch.

Crosstalk

A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

Bandwidth The frequency at which the output is attenuated by 3 dB.

On Response The frequency response of the on switch.

Insertion Loss The loss due to the on resistance of the switch.

Total Harmonic Distortion + Noise (THD + N) The ratio of the harmonic amplitude plus noise of the signal to the fundamental.

AC Power Supply Rejection Ratio (ACPSRR)

The ratio of the amplitude of signal on the output to the amplitude of the modulation. This is a measure of the ability of the device to avoid coupling noise and spurious signals that appear on the supply voltage pin to the output of the switch. The dc voltage on the device is modulated by a sine wave of 0.62 V p-p.

OUTLINE DIMENSIONS

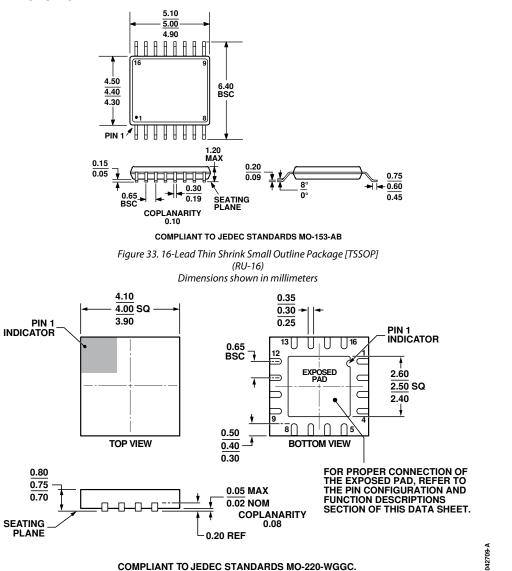


Figure 34. 16-Lead Lead Frame Chip Scale Package [LFCSP] 4 mm × 4 mm Body and 0.75 mm Package Height (CP-16-26) Dimensions shown in millimeters

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option
ADG1636BRUZ	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG1636BRUZ-REEL	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG1636BRUZ-REEL7	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG1636BCPZ-REEL	-40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16-26
ADG1636BCPZ-REEL7	-40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16-26

¹ Z = RoHS Compliant Part.

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